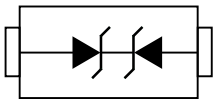
Description

The PESDUC5D5VB protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, low operating voltage. It gives designer the flexibilityto protect one bi-directional line in applications where arrays are not practical.



Feature

- 100W peak pulse power per line (t_P= 8/20μs)
- Bidirectional configurations
- Response time is typically < 1ns
- High ESD protection
- Low clamping voltage
- Transient protection for data lines to
  IEC 61000-4-2(ESD) ±18kV(air), ±15kV(contact);
  IEC 61000-4-4(EFT) 5A (5/50ns)

Applications

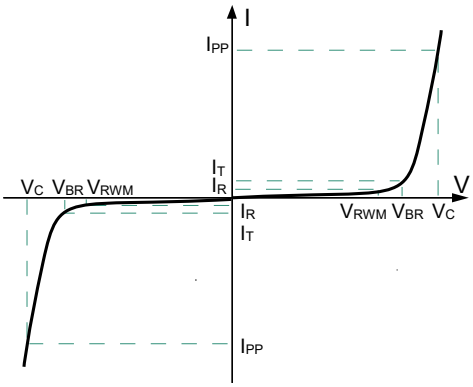
- Cellular phones
- Portable devices
- Digital cameras
- Power supplies
- Bidirectional configurations

Mechanical Characteristics

- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:260 ℃
- Device meets MSL 1 requirements
- Pure tin plating: 7 ~ 17 um
- Pin flatness：≤3mil

Electronics Parameter

Symbol	Parameter
V_{RWM}	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
P_{PP}	Peak Pulse Power
C_J	Junction Capacitance
I_F	Forward Current
V_F	Forward Voltage @ I_F



Electrical characteristics per line@25℃ (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Peak Reverse Working Voltage	V_{RWM}				5	V
Breakdown Voltage	V_{BR}	I_t = 1mA	5.6		8.5	V
Reverse Leakage Current	I_R	V_{RWM} = 5V , T=25℃			1.0	μA
Clamping Voltage[1)]	V_C	TLP = 16A , t_p = 100ns		28.1		V
Clamping Voltage[2)]	V_C	I_{PP} = 1A , t_P = 8/20μs			12	V
	V_C	I_{PP} = 5A , t_P = 8/20μs			20	V
Junction Capacitance	C_j	V_R=0V , f = 1MHz		0.4		pF

Notes:
1.TLP parameter: Z_0=50Ω, t_p=100ns, t_r=2ns, averaging window from 60ns to 80ns. R_{DYN} is calculated from 4A to 16A.
2.Non-repetitive current pulse, according to IEC61000-4-5.

Absolute maximum rating@25℃

Rating	Symbol	Value	Units
Peak Pulse Power (t_P = 8/20μs)	P_{PP}	100	W
Peak Pulse Current (t_P = 8/20μs)	I_{PP}	5	A
Lead Soldering Temperature	T_L	260 (10 sec)	℃
Junction and Storage Temperature Range	T_J,T_{STG}	-55~+150	℃
ESD Protection-Contact Discharge	V_{ESD}	±15	kV
ESD Protection-Air Discharge	V_{ESD}	±18	kV

Typical Characteristics

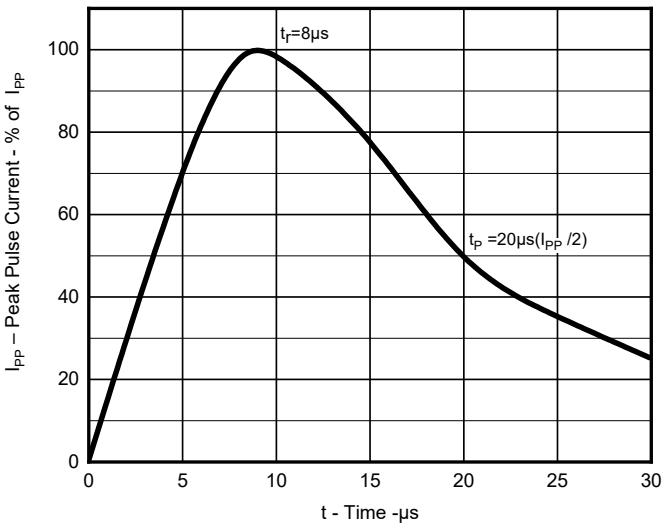


Fig 1.Pulse Waveform(8/20μs)

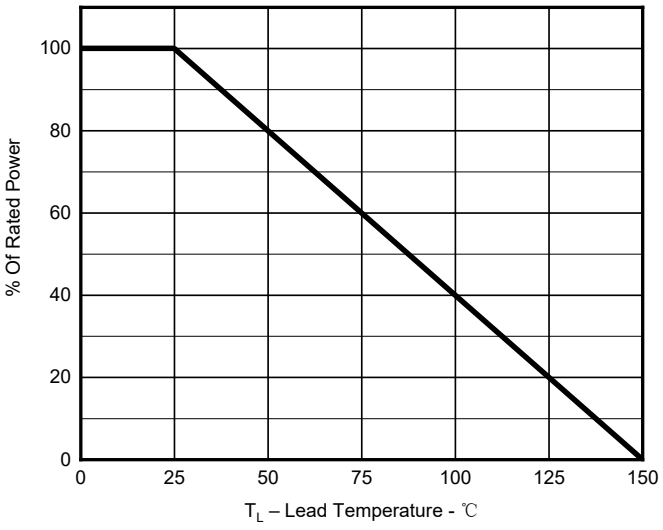


Fig 2.Power Derating Curve

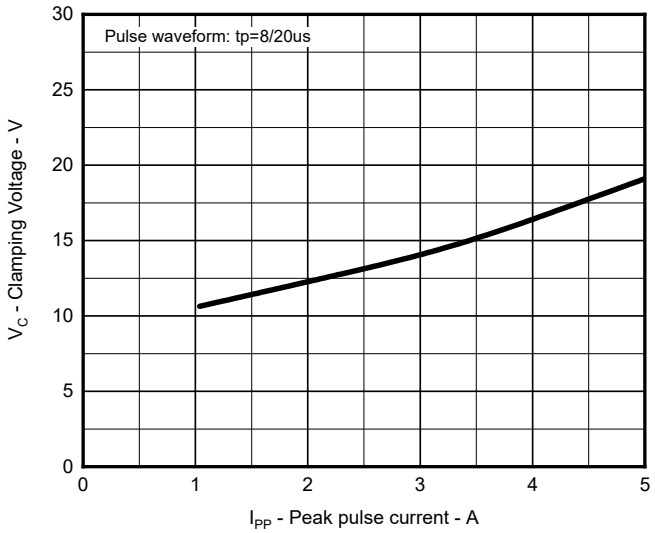


Fig 3. Clamping voltage vs. Peak pulse current

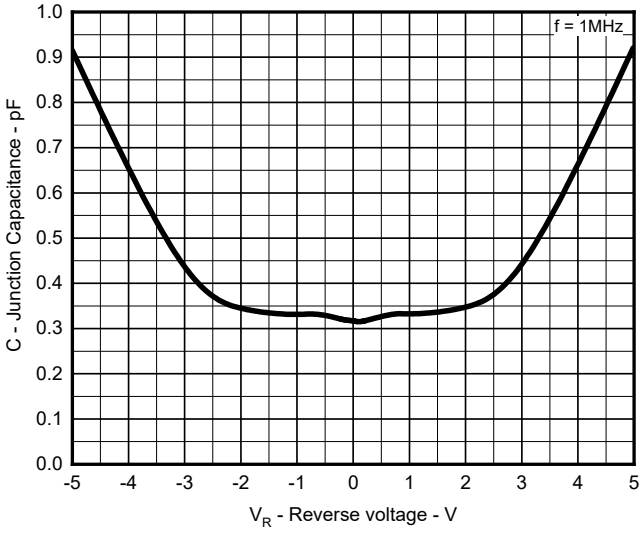


Fig 4. Capacitance vs. Reveres voltage

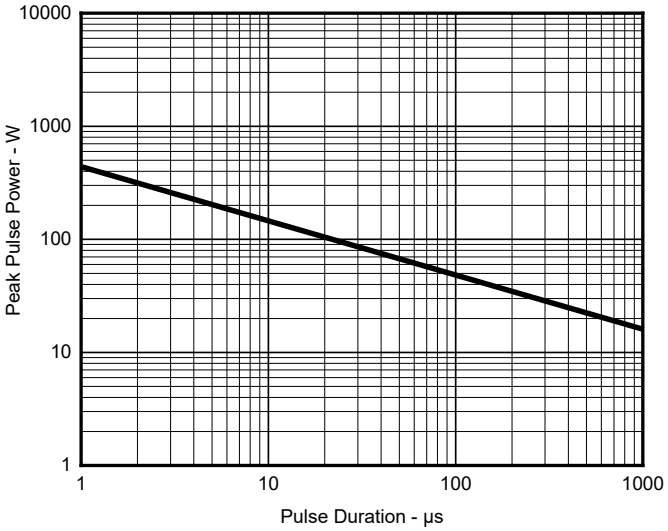


Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time

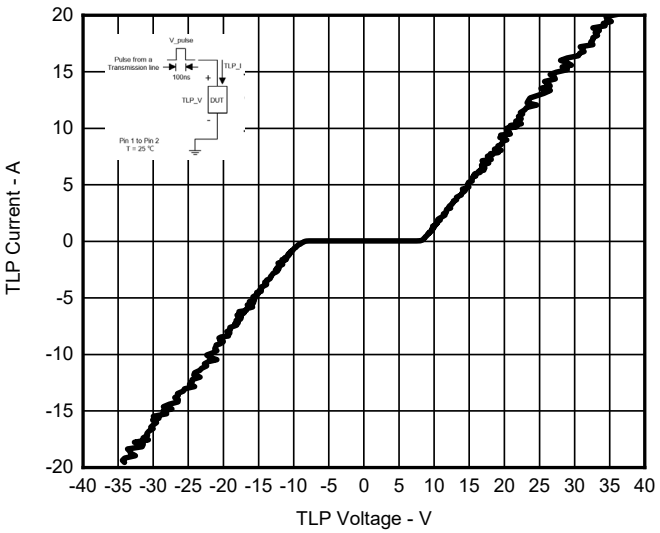
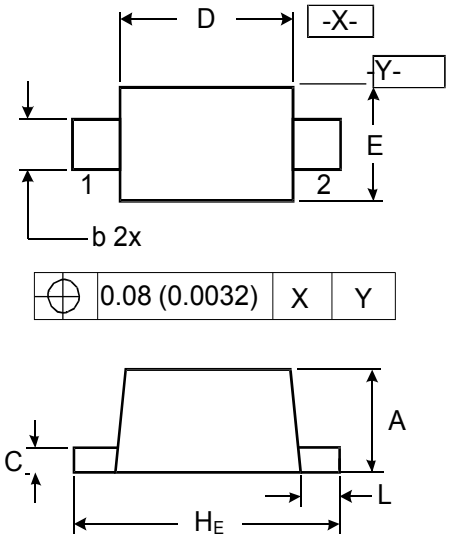


Fig 6. TLP Measurement

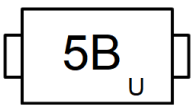
Outline Drawing – SOD-523



DIMENSIONS

SYMBOL	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	0.50	0.70	0.020	0.028
b	0.25	0.35	0.010	0.014
C	0.07	0.20	0.0028	0.0079
D	1.10	1.30	0.043	0.051
E	0.70	0.90	0.028	0.035
H_E	1.50	1.70	0.059	0.067
L	0.15	0.25	0.006	0.010

Marking



Ordering information

Order code	Package	Base qty	Delivery mode
UMW PESDUC5D5VB	SOD-523	3000	Tape and reel